TI-36447

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				U.S. PATENT DOC	UMENTS		
Exam.	Cite No.'	U.S. Patent Docu Number	rment Kind Code <sup>2</sup> (if known)	Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm- dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
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	,	OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS					
Exam. Cite Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, Initials* No. symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where publisher							
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		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS				
Exam. Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²			
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<u> </u>		"Free Energy Model for the Analysis of Bonding in a-Si <sub>x</sub> N <sub>y</sub> H <sub>z</sub> Alloys", Z. YIN and W. SMITH, J. Vac. Sci. Technol, A, Volume 9, No. 3, MayJune, 1991, pg. 972.				
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	U.S. PATENT DOCUMENTS									
Exam.	Cite No.1	U.S. Patent Do	Kind Code <sup>2</sup> (if known)	Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear				
ليد	AA	6,706,540	B2	Hikosaka et al.	03/16/2004	Entire Document				
Vh.	АВ	6,781,184	B2	Solayappan et al.	08/24/2004	Entire Document				
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Exam. Initials*	Cite No.1	Coffice   Number		Kind Code <sup>2</sup> (if known)	Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear			
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